

KSC5305DF NPN Silicon Transistor

Features

• High Voltage High Speed Power Switch

Application

- Built-in Free-wheeling Diode makes efficient anti saturation operation
- Suitable for half bridge light ballast Applications
- No need to interest an h_{FE} value because of low variable storage-time spread even though corner spirit product

Equivalent Circuit

• Low base drive requirement

Absolute Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector Base Voltage	800	V
V _{CEO}	Collector Emitter Voltage	400	V
V _{EBO}	Emitter Base Voltage	12	V
Ι _C	Collector Current (DC)	5	А
I _{CP}	*Collector Current (Pulse)	10	А
I _B	Base Current (DC)	2	А
I _{BP}	*Base Current (Pulse)	4	А
P _C	Power Dissipation (T _C =25°C)	40	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature range	-65 to +150	°C

Thermal Characteristics

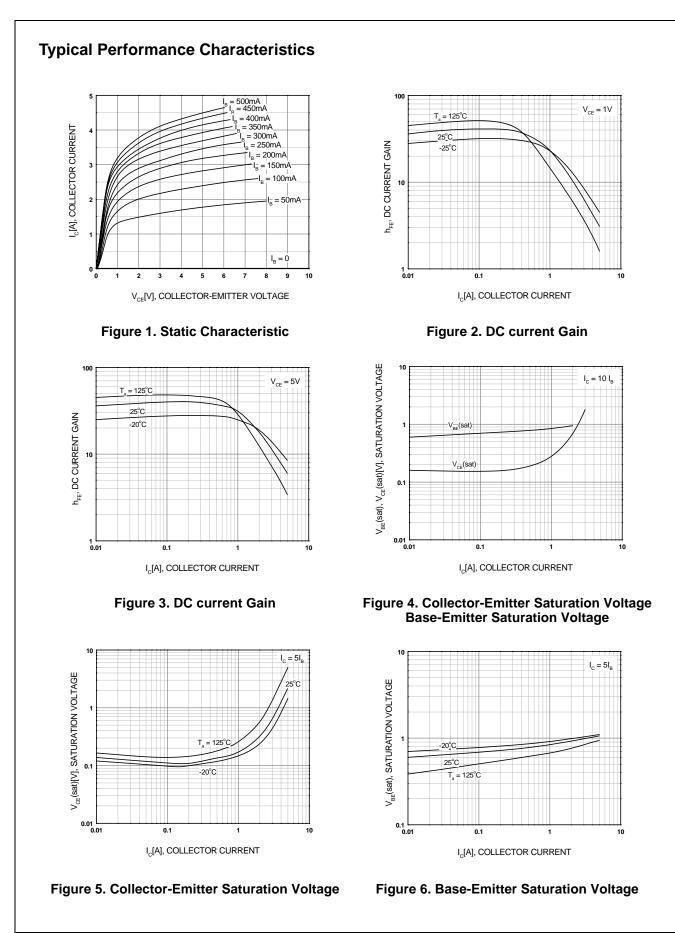
Symbol	Parameter	Rating	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	3.125	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	69.5	°C/W



1 **TO-220F** 1.Base 2.Collector 3.Emitter

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =1mA, I _E =0	800	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =5mA, I _B =0	400	-	-	V
BV_EBO	Emitter Cut-off Current	I _E =1mA, I _C =0	12	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} =500V, I _E =0	-	-	10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$	-	-	10	μΑ
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} =1V, I _C =0.8A V _{CE} =1V,I _C =2A	22 8	-	-	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =0.8A, I _B =0.08A I _C =2A, I _B =0.4A	-	-	0.4 0.5	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C =0.8A, I _B =0.08A I _C =2A, I _B =0.4A	-	-	1.0 1.0	V V
C _{ob}	Output Capacitance	V _{CB} = 10V, f=1MHz	-	-	75	pF
t _{ON}	Turn On Time	V _{CC} =300V, I _C =2A	-	-	150	ns
t _{STG}	Storage Time	I _{B1} = 0.4A, I _{B2} =-1A	-	-	2	μS
t _F	Fall Time	R _L = 150Ω	-	-	0.2	μS
t _{STG}	Storage Time	V _{CC} =15V,V _Z =300V	-	-	2.25	μS
t _F	Fall Time	$I_{C} = 2A, I_{B1} = 0.4A$ $I_{B2} = -0.4A, L_{C} = 200 \mu H$	-	-	150	ns
V _F	Diode Forward Voltage	I _F = 1A I _F = 2A	-	-	1.5 1.6	V V
t _{rr}	* Reverse recovery time (di/dt = 10A/μs)	$I_F = 0.4A$ $I_F = 1A$ $I_F = 2A$	- -	800 1.4 1.9		ns μs μs

* Pulse Test : Pulse Width=5mS, Duty cycles \leq 10%



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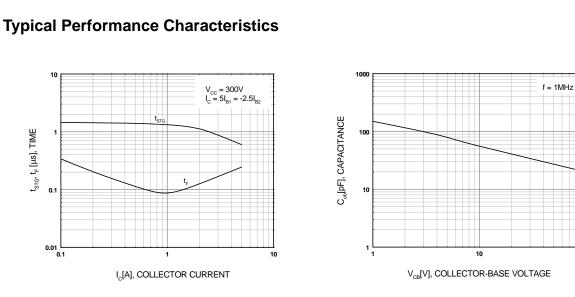


Figure 7. Switching Time

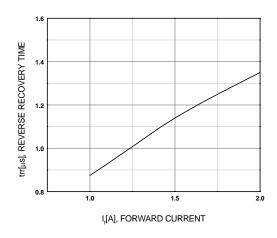
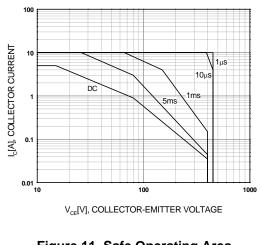


Figure 9. Reverse Recovery Time



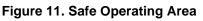


Figure 8. Collector Output Capacitance

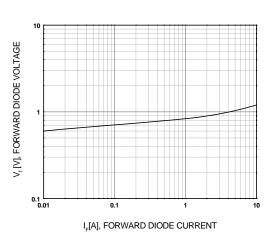


Figure 10. Forward Diode Voltage

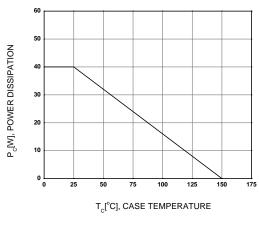
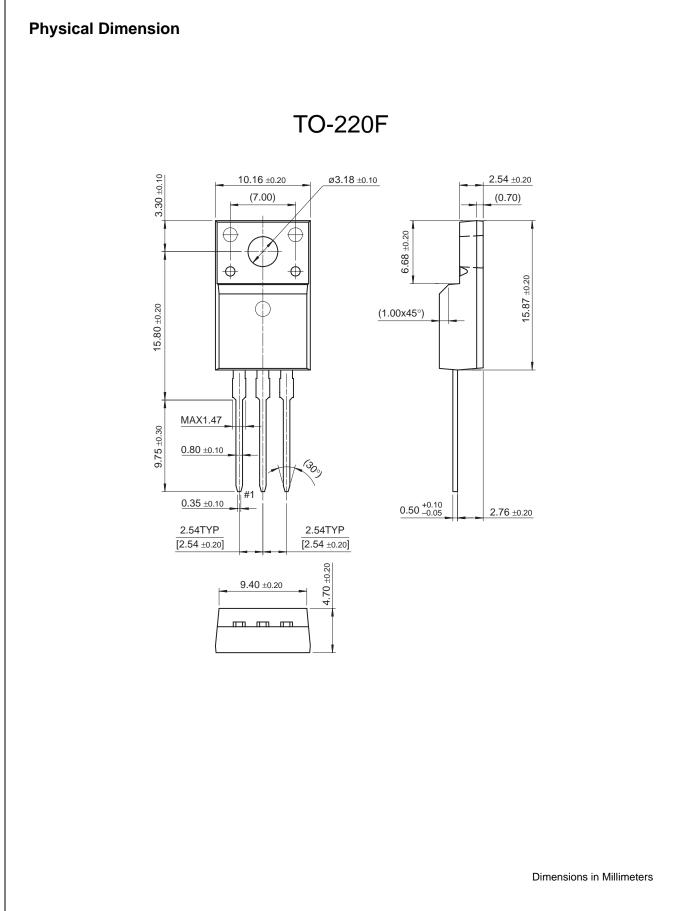


Figure 12. Power Derating

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